**TOSHIBA** U2GWJ44

### TOSHIBA SCHOTTKY BARRIER RECTIFIER SCHOTTKY BARRIER TYPE

## U 2 G W J 4 4

#### SWITCHING POWER SUPPLY APPLICATION

 $: V_{FM} = 0.55V \text{ (Max.)}$ Low Forward Voltage

Average Forward Current  $: I_{F(AV)} = 2.0A$ 

Repetitive Peak Reverse Voltage  $: V_{RRM} = 40V$ 

Surface Mounting Plastic Mold Package

### **MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	$v_{RRM}$	40	V
Average Forward Current	I <sub>F (AV)</sub>	2.0	Α
Peak One Cycle Surge Forward Current (Non-Repetitive)	I <sub>FSM</sub>	40 (50Hz)	A
Junction Temperature	$T_{\rm j}$	-40~125	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-40~125	$^{\circ}\mathrm{C}$

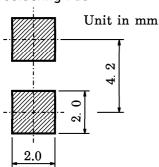
# Unit in mm 2 + 0.2 1.5 ± 0.2 0.2 1. ANODE 2. CATHODE **JEDEC EIAJ** TOSHIBA 3-4D1A

Weight: 0.06g

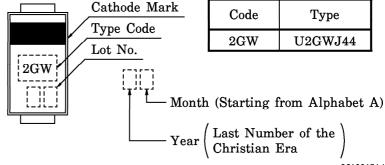
### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

	ı	I		1		
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$V_{ extbf{FM}}$	$I_{\text{FM}} = 2.0 \text{A}$	_	_	0.55	V
Repetitive Peak Reverse Current	$I_{RRM}$	$V_{ m RRM} = 40 V$	_	_	500	$\mu$ <b>A</b>
Junction Capacitance	$C_{j}$	$V_R = 10V$ , $f = 1.0MHz$	_	125	_	рF
Thermal Resistance	70.7 (1)	On ceramic substrate		_	60	°C/W
(Junction to Ambient)	rth (j-a)	On glass-epoxy substrate	_		145	[ C / W

### Standard Soldering Pad



### **MARKING**

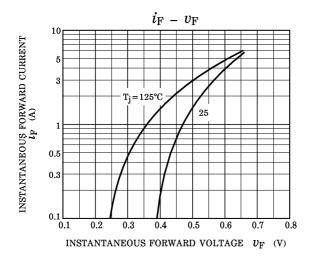


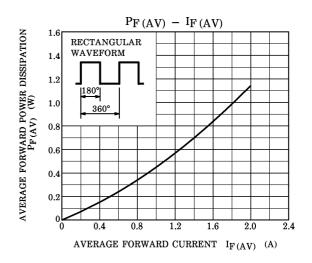
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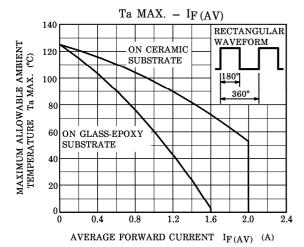
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		ON CERAMIC SUBSTRATE	ON GLASS-EPOXY SUBSTRATE	
Soldering land	: a	2mm×2mm	6mm×6mm	
Substrate size	: b	50mm×50mm	50mm×50mm	
Substrate thickness	: c	0.64mm	1.6mm	
c c b				

